









Release Date: 24 June 2025 Version: A00

PRODUCT DATASHEET



- ► DC-In Solid State Relay
- ► DIP7 Gullwing 400mil
- Zero-Cross TRIAC Output

TDRX213(M)-GV





TDRX213(M) Series

DESCRIPTION:





The TDRX213(M) series combine an AlGaAs infrared emitting diode as the emitter which is optically coupled to a monolithic silicon zero-cross photo TRIAC to drive a power TRIAC in a plastic DIP7 package with Gullwing lead forming option.

FEATURES:

- High isolation 5000Vrms
- DC input with TRIAC output
- Operating temperature range -40°C to +85°C
- **REACH & RoHS compliance**
- MSL class 1
- **Regulatory Approvals:**
 - UL UL1577
 - VDE EN60747-5-5 (VDE0884-5)
 - CQC GB4943.1, GB8898
 - cUL CSA Component Acceptance Service Notice 5A
- Packing: 45pcs/tube

APPLICATIONS:

- Solenoid/valve controls
- Lighting controls
- Motor controls
- Temperature controls
- Static AC power switches
- Solid state relays
- Interfacing microprocessors to 115 to 240VAC peripherals













NAMING & ORDERING INFORMATION:

Naming Information:

TDR X 213 (M) - G V		
TDRX213	Part Number	
×	Selection: On-State RMS Current (X=0~3)	
M	Lead Form Option: DIP7 Gullwing	
G	Green Option	
V	VDE Option	

Ordering Information:

TDRX213(M)-GV

 \underline{X} = Selection: On-State RMS Current (X=0~3)

Dort Number	Cumbal	Values		Lloit	Tost Condition	
Part Number	Symbol	Min.	Тур.	Max.	Unit	Test Condition
TDR0213(M)-GV	IT _(RMS) *			0.3	А	I _{TSM} =3A ** P _W =100μs, 120pps
TDR1213(M)-GV				0.6		I _{TSM} =6A P _W =100μs, 120pps
TDR2213(M)-GV				0.9		I _{TSM} =9A P _W =100μs, 120pps
TDR3213(M)-GV				1.2		I _{TSM} =12A P _W =100μs, 120pps

^{*} $IT_{(RMS)}$ = On-State RMS Current

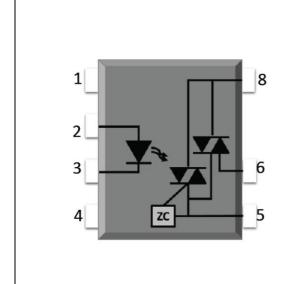
Version No.	Original Release Date		
Rev: A00	29/08/2024		

^{**} I_{TSM} = Non-repetitive Surge Current



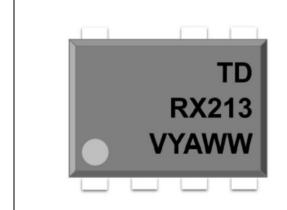
SCHEMATIC DIAGRAM & MARKING:

Schematic Diagram:



PIN Definition			
1	NC		
2	Anode		
3	Cathode		
4	NC		
5	Gate		
6	Terminal		
7	(Absent)		
8	Terminal		

Marking Information:



Marking Definition			
TD	Manufacturer Code		
RX213	Part Number		
V	VDE Applicable		
Υ	Fiscal Year		
А	Manufacturing Code		
WW	Work Week		

Labelling Information:



This product is manufactured, tested, and packed by



for more details, please visit www.tdled.com



ABSOLUTE CHARACTERISTICS:

Absolute Maximum Ratings:

Parameter		Symbol	Ratings	Unit	
		INPUT			
Forward Current		lF	60	mA	
Reverse Voltage		V _R	6	٧	
Junction Temperature		Tj	125	°C	
Input Power Dissipation		Pı	100	mW	
		OUTPUT			
Off-State Output Terminal Voltag	e	V _{DRM}	600	V	
	TDR0213		0.3		
On-State RMS Current	TDR1213	- I _{T(RMS)}	0.6	А	
on-state rivis current	TDR2213	TT(RIVIS)	0.9		
	TDR3213		1.2		
	TDR0213		3		
Non-repetitive Surge Current	TDR1213	- I _{TSM}	6	Α	
P _w =100μs, 120pps	TDR2213	IISM	9		
	TDR3213		12		
Junction Temperature		Tj	125	°C	
	(COMMON			
Total Power Dissipation		P _{tot}	400	mW	
Isolation Voltage		V _{iso}	5000 *1	Vrms	
Operating Temperature		Topr	-40~+85	°C	
Storage Temperature		T _{stg}	-40~+125	°C	
Soldering Temperature		T _{sol}	260 *²	°C	

^{*1.} AC for 1 minute, R.H.= $40^{\sim}60\%$.

^{*2.} For 10 seconds max.



ELECTRICAL CHARACTERISTICS:

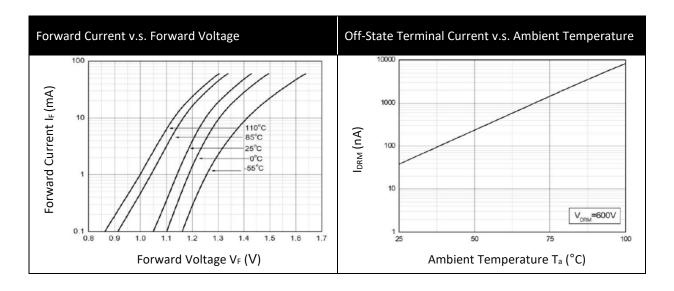
Electrical Optical Characteristics at T_a=25°C:

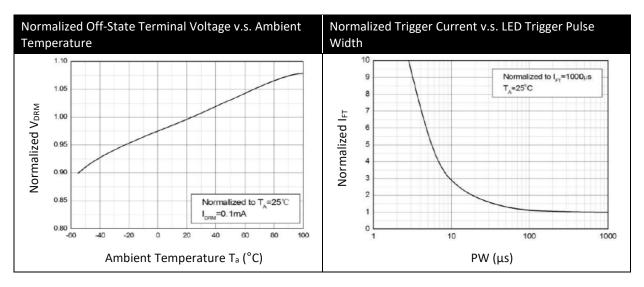
Parameter	Symbol		Values		Unit	Test Condition
rarameter	3,111301	Min.	Тур.	Max.	01110	rest contained
		INPU [*]	Т			
Forward Voltage	V _F		1.24	1.4	V	I _F =10mA
Reverse Current	I _R			10	μΑ	V _R =6V
Input Capacitance	Cin		30		pF	V=0, f=1kHz
		OUTPL	JT			
Peak Off-State Current Either Direction	I _{DRM}			100	μА	V _{DRM} =600V I _F =0
On-State Terminal Voltage	V_{TM}		1.7	2.5	V	I _{TM} =Rated I _{TM}
Critical Rate of Rise of Off-State Voltage - Breakdown Voltage	dV/dt	1000			V	V _{PEAK} =600V *1
	TRA	NSFER CHAR	ACTERISTICS			
LED Trigger Current	I _{FT}			10	mA	R _L =100Ω Terminal Voltage=6V
Holding Current	I _H			25	mA	
Isolation Resistance	R _{ISO}	10^12	10^14		Ω	DC=500V, 40~60% R.H.
Floating Capacitance	Cıo		0.25	1	pF	V=0, f=1MHz
ZERO-CROSSING CHARACTERISTICS						
Inhibit Voltage	V _{INH}			20	V	I _F =10mA
Leakage in Inhibited State	I _{DRM2}			500	μΑ	I _F =10mA V _{DRM} =600V
Response Time (Rise)	Ton		30		μs	$V_D=6V$, $R_L=100\Omega$ $I_F=10$ mA

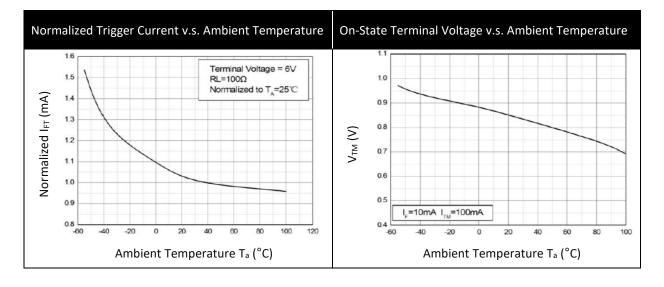
^{*1.} Test voltage must be applied within dV/dt rating.



CHARACTERISTIC CURVES:

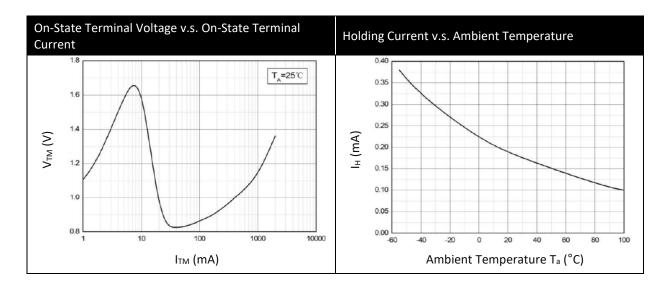


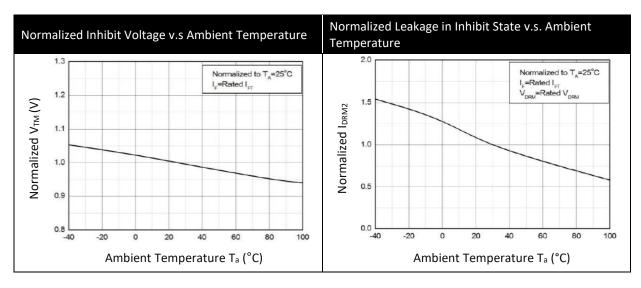


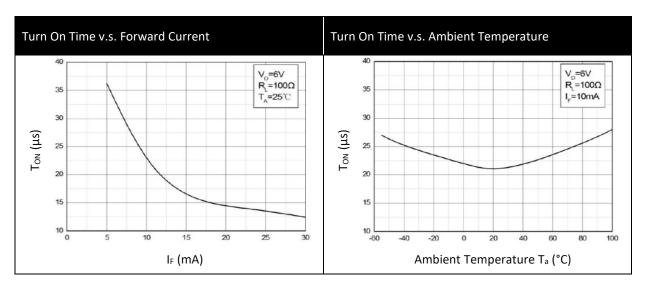




CHARACTERISTIC CURVES:



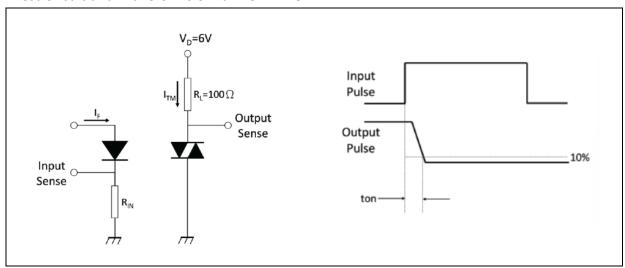




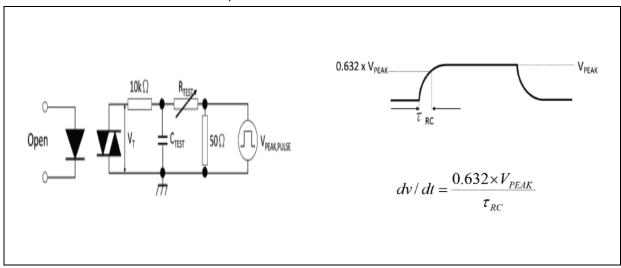


TEST CIRCUIT:

Test Circuit and Waveforms of Turn On Time:



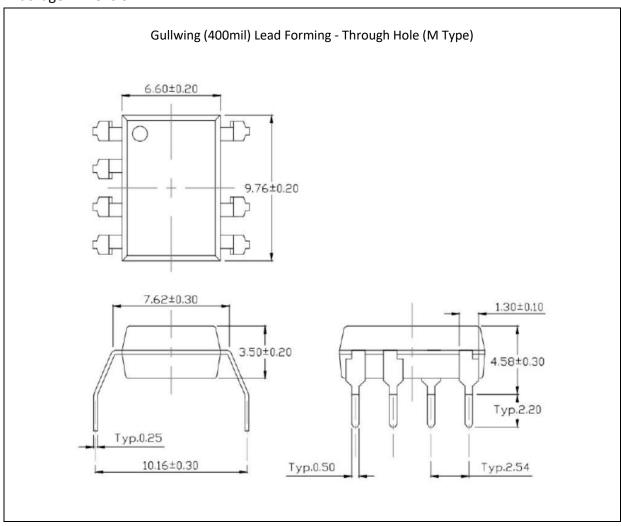
Test Circuit and Waveforms of dV/dt:





OUTLINE DIMENSION:

Package Dimension:

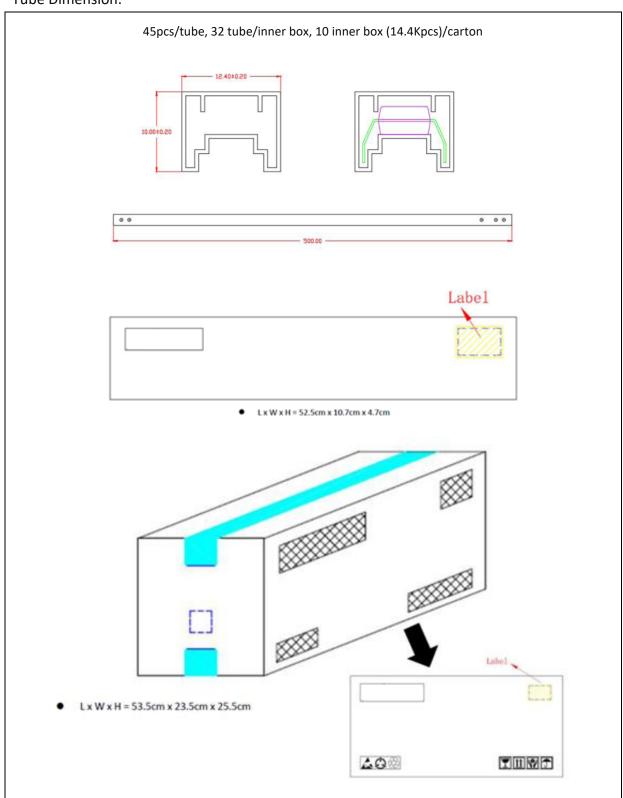


1. All dimensions are in millimetre (mm).



PACKING SPECIFICATION:

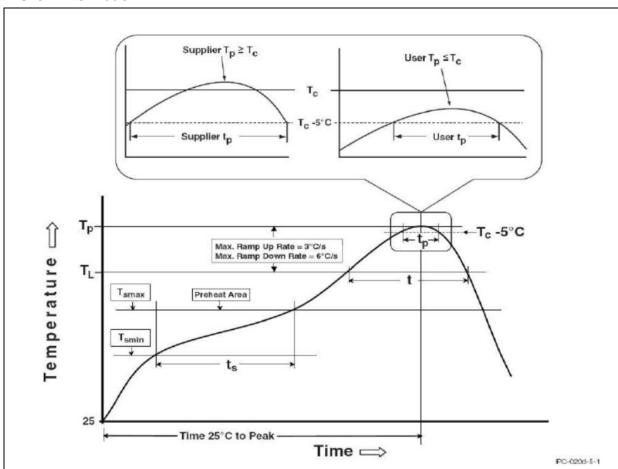
Tube Dimension:





RECOMMENDED SOLDERING PROFILE:

Reflow Information:

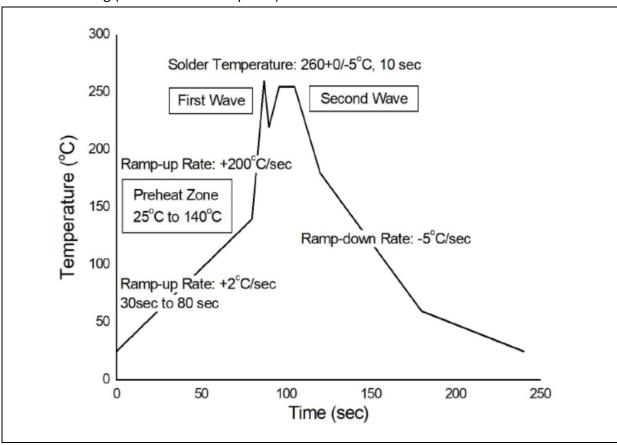


Profile Feature	Sn-Pb Assembly Profile	Pb-Free Assembly Profile
Temperature Min. (T _{smin})	100°C	150°C
Temperature Max. (T _{smax})	150°C	200°C
Time (t _s) from (T _{smin} to T _{smax})	60-120 seconds	60-120 seconds
Ramp-up Rate (t∟ to t _P)	3°C/second max.	3°C/second max.
Liquidous Temperature (T _L)	183°C	217°C
Time (t _L) Maintained Above (T _L)	60-150 seconds	60-150 seconds
Peak Body Package Temperature	235°C +0°C / -5°C	260°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	20 seconds	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.



RECOMMENDED SOLDERING PROFILE:

Wave Soldering (JESD22-A111 Compliant):



Hand Soldering:

Soldering Temperature	380±5°C
Soldering Time	3 sec max.

Note:

- One time soldering is recommended for all soldering methods.
- Do not solder more than three times for IR reflow soldering.